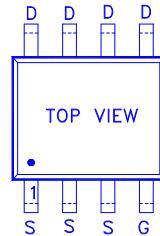
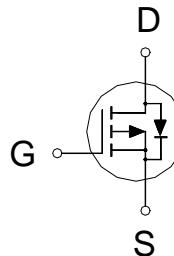


**NIKO-SEM**
**P-Channel Logic Level Enhancement  
Mode Field Effect Transistor**
**P2003EVG**  
**SOP-8**  
**Halogen-Free & Lead-Free**
**PRODUCT SUMMARY**

$V_{(BR)DSS}$	$R_{DS(ON)}$	$I_D$
-30	20mΩ	-9A


 4 : GATE  
 5,6,7,8 : DRAIN  
 1,2,3 : SOURCE
**ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$  Unless Otherwise Noted)****100% UIS tested**

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		$V_{DS}$	-30	V
Gate-Source Voltage		$V_{GS}$	$\pm 25$	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	$I_D$	-9	A
	$T_C = 70^\circ\text{C}$		-7	
Pulsed Drain Current <sup>1</sup>		$I_{DM}$	-50	
Avalanche Current		$I_{AS}$	-26	
Avalanche Energy	$L = 0.1\text{mH}$	$E_{AS}$	34	mJ
Power Dissipation	$T_C = 25^\circ\text{C}$	$P_D$	2.5	W
	$T_C = 70^\circ\text{C}$		1.6	
Operating Junction & Storage Temperature Range		$T_j, T_{stg}$	-55 to 150	°C

**THERMAL RESISTANCE RATINGS**

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		25	°C / W
Junction-to-Ambient	$R_{\theta JA}$		50	°C / W

<sup>1</sup>Pulse width limited by maximum junction temperature.
**ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ , Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
<b>STATIC</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$	-30			V
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-1	-1.5	-3	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{V}, V_{GS} = \pm 25\text{V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -24\text{V}, V_{GS} = 0\text{V}$			-1	$\mu\text{A}$
		$V_{DS} = -20\text{V}, V_{GS} = 0\text{V}, T_J = 125^\circ\text{C}$			-10	
On-State Drain Current <sup>1</sup>	$I_{D(\text{ON})}$	$V_{DS} = -5\text{V}, V_{GS} = -10\text{V}$	9			A
Drain-Source On-State Resistance <sup>1</sup>	$R_{DS(\text{ON})}$	$V_{GS} = -4.5\text{V}, I_D = -7\text{A}$	25	35		$\text{m}\Omega$
		$V_{GS} = -10\text{V}, I_D = -9\text{A}$	15	20		

**NIKO-SEM****P-Channel Logic Level Enhancement  
Mode Field Effect Transistor****P2003EVG**

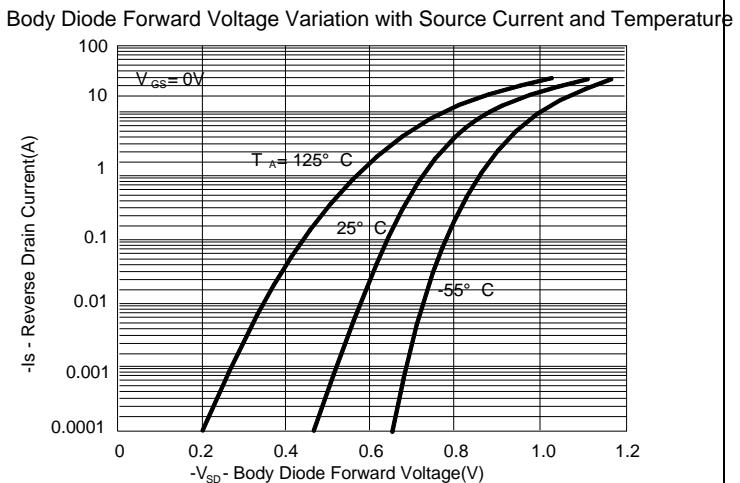
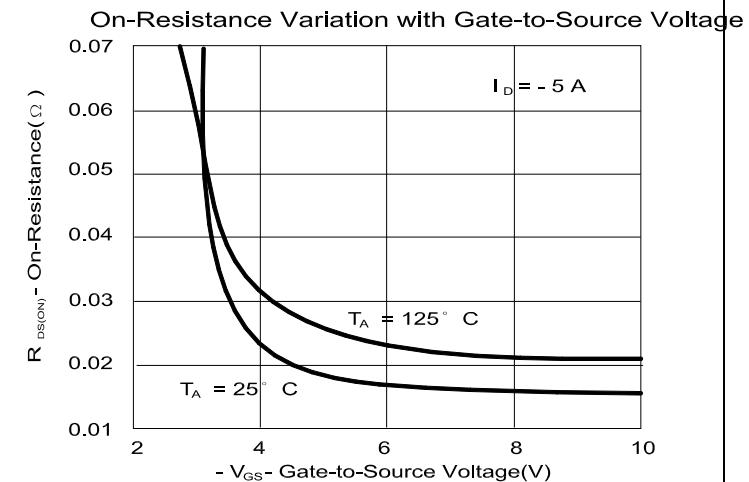
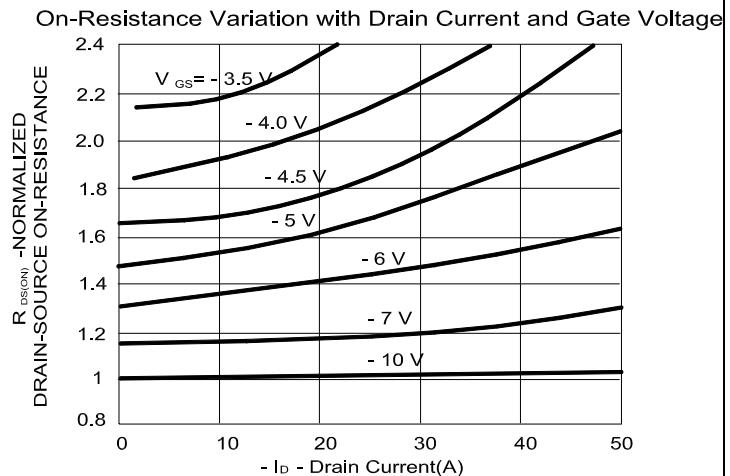
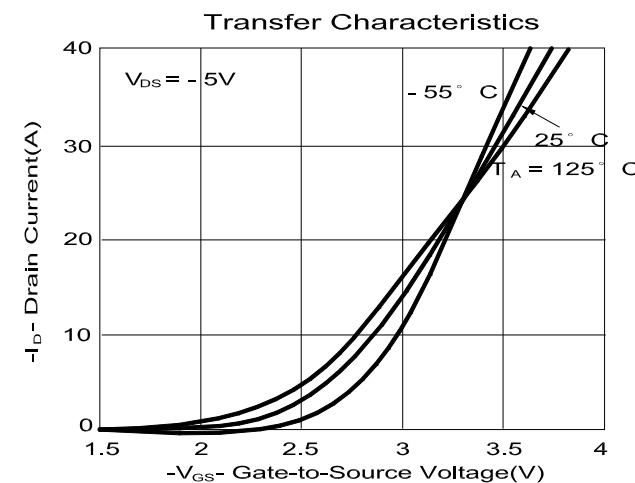
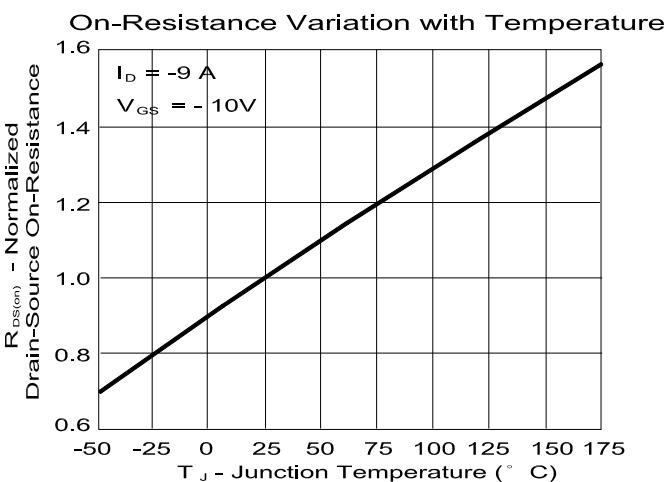
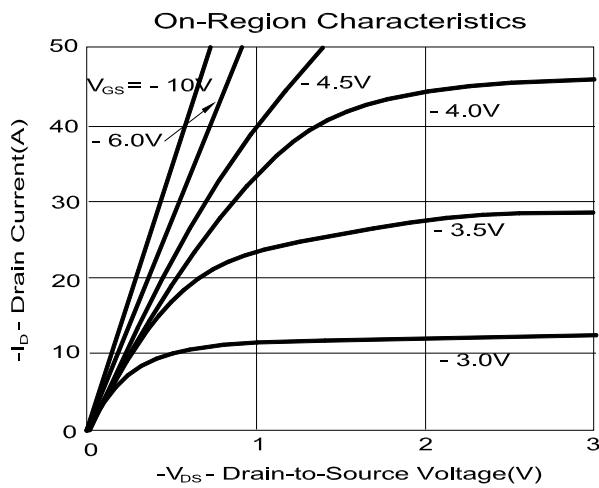
SOP-8

Halogen-Free &amp; Lead-Free

Forward Transconductance <sup>1</sup>	$g_{fs}$	$V_{DS} = -10V, I_D = -9A$		24		S
<b>DYNAMIC</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = -15V, f = 1MHz$		1610		pF
Output Capacitance	$C_{oss}$			410		
Reverse Transfer Capacitance	$C_{rss}$			200		
Gate Resistance	$R_g$	$V_{GS} = 15mV, V_{DS} = 0V, f = 1MHz$		3.7		$\Omega$
Total Gate Charge <sup>2</sup>	$Q_g$	$V_{DS} = 0.5V_{(BR)DSS}, V_{GS} = -10V,$ $I_D = -9A$		31.4		nC
Gate-Source Charge <sup>2</sup>	$Q_{gs}$			4.5		
Gate-Drain Charge <sup>2</sup>	$Q_{gd}$			8.2		
Turn-On Delay Time <sup>2</sup>	$t_{d(on)}$	$V_{DS} = -15V, R_L = 1\Omega$ $I_D \approx -1A, V_{GS} = -10V, R_{GS} = 6\Omega$		5.7		nS
Rise Time <sup>2</sup>	$t_r$			10		
Turn-Off Delay Time <sup>2</sup>	$t_{d(off)}$			18		
Fall Time <sup>2</sup>	$t_f$			5		
<b>SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (<math>T_C = 25^\circ C</math>)</b>						
Continuous Current	$I_S$				-2.1	A
Forward Voltage <sup>1</sup>	$V_{SD}$	$I_F = -1A, V_{GS} = 0V$			-1.2	V

<sup>1</sup>Pulse test : Pulse Width  $\leq 300 \mu sec$ , Duty Cycle  $\leq 2\%$ .<sup>2</sup>Independent of operating temperature.

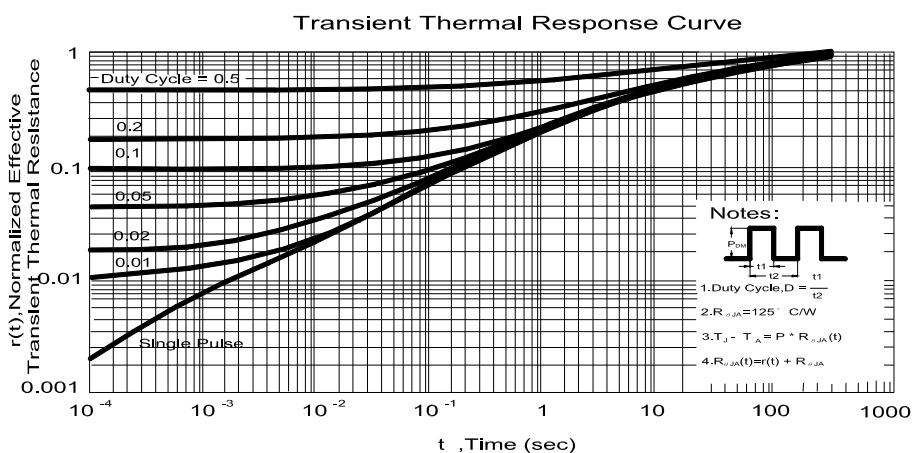
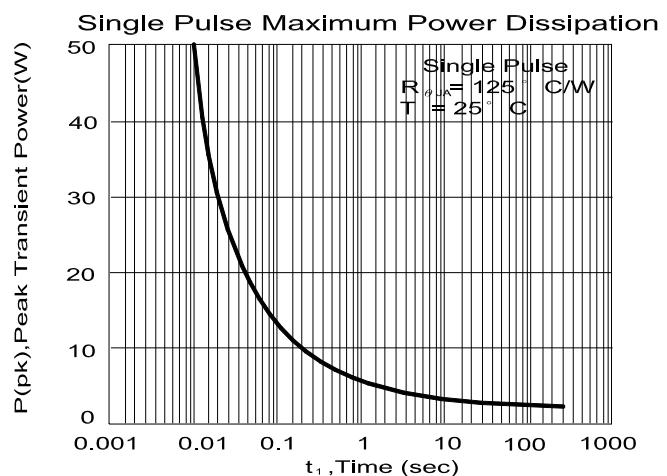
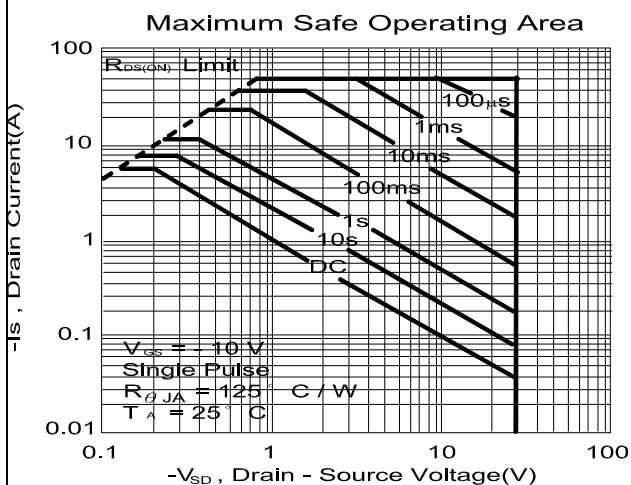
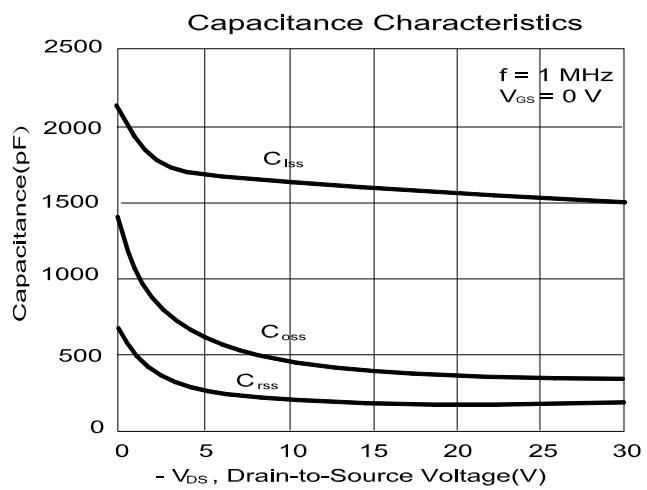
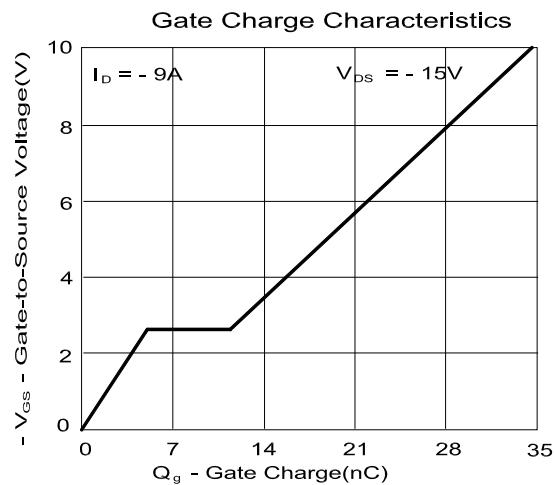
REMARK: THE PRODUCT MARKED WITH "P2003EVG", DATE CODE or LOT #

**NIKO-SEM****P-Channel Logic Level Enhancement  
Mode Field Effect Transistor****P2003EVG  
SOP-8  
Halogen-Free & Lead-Free**

**NIKO-SEM**

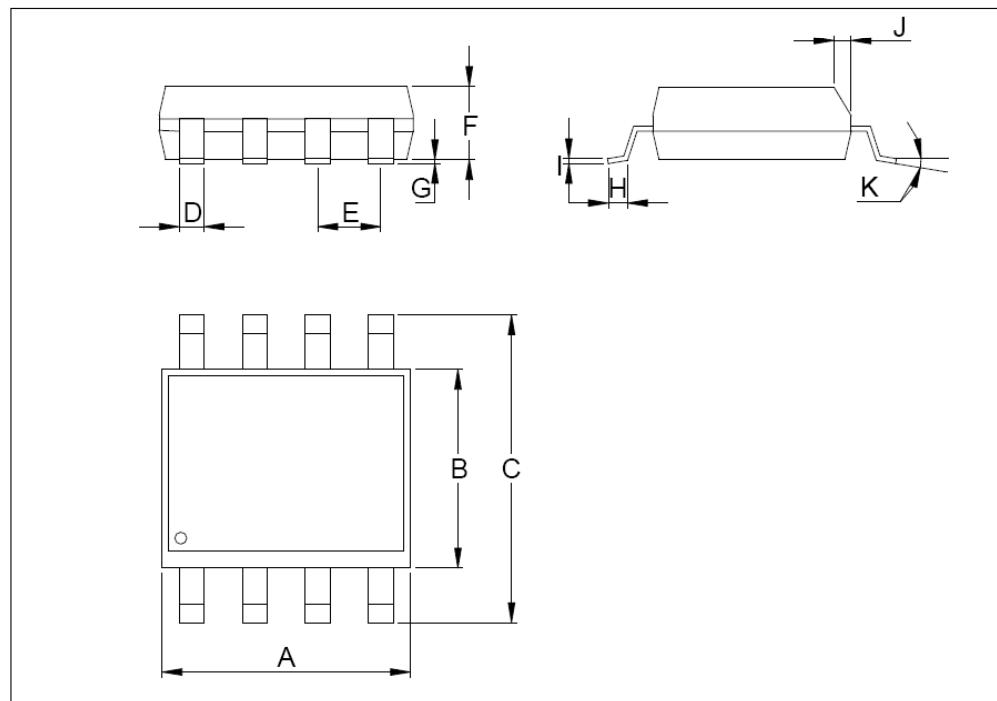
# P-Channel Logic Level Enhancement Mode Field Effect Transistor

**P2003EVG**  
SOP-8  
Halogen-Free & Lead-Free



**NIKO-SEM****P-Channel Logic Level Enhancement  
Mode Field Effect Transistor****P2003EVG  
SOP-8  
Halogen-Free & Lead-Free****SOIC-8(D) MECHANICAL DATA**

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.8	4.9	5.0	H	0.4	0.715	0.83
B	3.8	3.9	4.0	I	0.19	0.22	0.25
C	5.8	6.0	6.2	J	0.25	0.375	0.5
D	0.33	0.445	0.51	K	0°	4°	8°
E		1.27		L			
F	1.25	1.375	1.62	M			
G	0.1	0.175	0.25	N			



# X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [MOSFET](#) category:*

*Click to view products by [NIKO](#) manufacturer:*

Other Similar products are found below :

[614233C](#) [648584F](#) [MCH3443-TL-E](#) [MCH6422-TL-E](#) [FDPF9N50NZ](#) [FW216A-TL-2W](#) [FW231A-TL-E](#) [APT5010JVR](#) [NTNS3A92PZT5G](#)  
[IRF100S201](#) [JANTX2N5237](#) [2SK2464-TL-E](#) [2SK3818-DL-E](#) [FCA20N60\\_F109](#) [FDZ595PZ](#) [STD6600NT4G](#) [FSS804-TL-E](#) [2SJ277-DL-E](#)  
[2SK1691-DL-E](#) [2SK2545\(Q,T\)](#) [D2294UK](#) [405094E](#) [423220D](#) [MCH6646-TL-E](#) [TPCC8103,L1Q\(CM](#) [367-8430-0972-503](#) [VN1206L](#)  
[424134F](#) [026935X](#) [051075F](#) [SBVS138LT1G](#) [614234A](#) [715780A](#) [NTNS3166NZT5G](#) [751625C](#) [873612G](#) [IRF7380TRHR](#)  
[IPS70R2K0CEAKMA1](#) [RJK60S3DPP-E0#T2](#) [RJK60S5DPK-M0#T0](#) [APT5010JVFR](#) [APT12031JFLL](#) [APT12040JVR](#) [DMN3404LQ-7](#)  
[NTE6400](#) [JANTX2N6796U](#) [JANTX2N6784U](#) [JANTXV2N5416U4](#) [SQM110N05-06L-GE3](#) [SIHF35N60E-GE3](#)